

1. Scope :

This specification applies to PIN silicon photodiode chips.
Device No. PD-3A091-B.

2. Structure :

- 2-1. Planar type : PIN diode.
- 2-2. Electrodes :
Top side (Anode) : Aluminum alloy.
Back side (Cathode) : Gold.

3. Size :

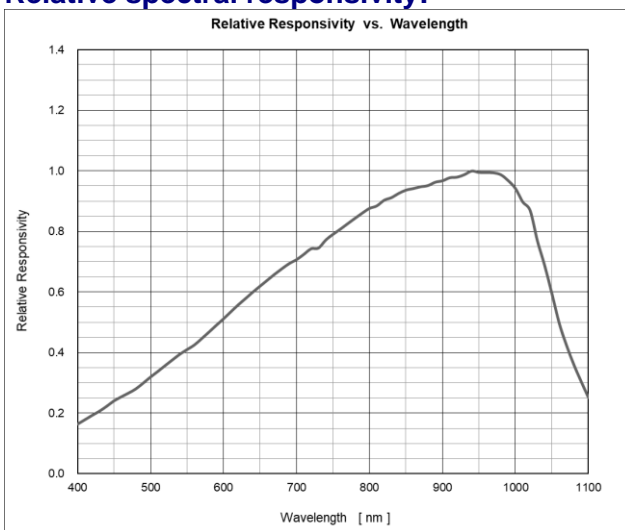
- 3-1. ^{*1}Chip size: 90.55 mils x 90.55 mils (2.30 mm x 2.30 mm)
- 3-2. Chip thickness : 13.77 ± 1.00 mils (0.350 mm ± 0.025 mm)
- 3-3. Active area : 48.81 mils x 13.38 mils x 4 element (1.24 mm x 0.34 mm x 4 element)
- 3-4. Bonding pad (Anode) : 6.29 mils x 7.87 mils x 4 element
(0.160 mm x 0.200 mm x 4 element)
- 3-5. Pattern drawing : Refer to the attached drawing
^{*1}Including scribing line. The chip size is about (2.275 ± 0.025) x (2.275 ± 0.025) mm² after dicing.

4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
^{**} Reverse dark Current	I _D	V _R =20V E _e =0mW/cm ²			5	nA
^{**} Reverse breakdown voltage	V _{(BR)R}	I _R =100uA E _e =0mW/cm ²	40			V
^{**} Forward Voltage	V _F	I _F =20mA E _e =0mW/cm ²			1.2	V
Total Capacitance	C _t	V _R =5V E _e =0mW/cm ² f=1MHz		4.5		pF

^{**}Based on 100% probing

5. Relative spectral responsivity:



^{**}Bare chip measured with integrating sphere, for reference only.

